

EAST - (10781035 asymmetrical intergate insul.wsp.1)

File View Edit Tools Window Help

Drafts

- BRS:
- BRS:
- BRS:
- BRS: knall
- BRS: 19 21 29
- BRS: 32 with 33

Pending

Active

- 11:121 "561905T".pn

Failed

- (floating adj) (plate trap\$4) (charge near (trap\$4 storage))

Saved

- S1: 111 09/048877
- S2: 117361 "KONINKLIJKE PHILIPS".as
- S3: 17761 (intergate inter adj gate) near2 (insulat\$5 dielectric oxide)
- S4: 1101024 (aluminium adj oxide "al.sub.20.sub.3")
- S5: 1130461 ("al.sub.20.sub.3")
- S6: 1171 (intergate inter adj gate) near2 (insulat\$5 dielectric oxide) (clm.)
- S7: 13021 (intergate inter adj gate) near2 (insulat\$5 dielectric oxide) (clm.)
- S8: 1104201 (aluminium adj oxide "al.sub.20.sub.3") (clm.)
- S9: 1171 (intergate inter adj gate) near2 (insulat\$5 dielectric oxide) (clm.)
- S10: 131 "6142248"
- S11: 121 "6142248".pn
- S12: 121 "6141248".pn
- S13: 191 "6160206".pn

561905T.pn

Mary 2005

U	I	Inventor	Document	Issn	P	Title	Current	Current	I	Retrieval	S	C	P	Image	Def
1	P	Endo, Nobu	US 5619051:19970-11	Semiconductor nonvolatile memory	ce	257/31	257/324				P				US 561905
2	P	ENDO, N	US 5619051:19970	Floating gate type non-volatile memor							P				

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5/2/04

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